

XG0083

N-Channel Enhancement Mode SGT MOSFET

60V(VDS) / ± 20 V(VGS) / 270A(ID)

Rev0.1

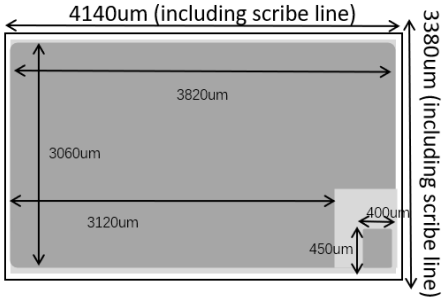
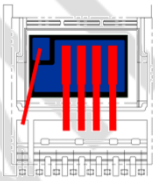


Wafer Specification

1. Order Information

Part No.	Description	Gross die / per 8,, wafer
XG0083	60V(V_{DS}) / $\pm 20V(V_{GS})$ / 270A(I_D) N-Channel Enhancement Mode SGT MOSFET	1,972

2. Physical Characteristics

	Die Size: 4140 μ m $\times$ 3380 μ m (including scribe line)
	Gate: 400 μ m $\times$ 450 μ m
	For TOLL package Suggest Bonding wire: Gate: 1*5mil AL Source: 4*20mil AL 

3. Mechanical Data

Nominal Back Metal Composition, Thickness	Ti-Ni-Ag (1kA°-3kA°-10kA°)
Nominal Front Metal Composition, Thickness	ALCu (5.5 μ m)
Wafer Diameter	200mm, with 010 notch
Wafer Thickness	150 μ m $\pm$ 10 μ m
Scribe Line Width	80 μ m

4. Key Electrical Characteristics of Die (at $T_J = 25^\circ\text{C}$, unless otherwise specified)

Parameter	Description	Min.	Typ.	Max.	Unit	Test Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	60	-	-	V	V _{GS} =0V, I _D =250μA
I _{D(Device Ref)}	Continuous Drain Current	-	-	270	A	T _J =25 °C
R _{DS(on)} (FT)	Static Drain-to-Source On-Resistance	-	1.2	1.5	mΩ	V _{GS} =10V, I _D =15A
V _{GS(th)}	Gate Threshold Voltage	2.5	2.8	3.2	V	V _{DS} =V _{GS} , I _D =250μA
I _{DSS}	Drain-to-Source Leakage Current	-	-	1	μA	V _{DS} =60V, V _{GS} =0V
I _{GSS}	Gate-to-Source Leakage Current	-	-	±100	nA	V _{GS} =±20V, V _{DS} =0V
E _{AS}	Single Pulsed Avalanche Energy	-	-	990	mJ	L=0.5mH, V _{DD} =30V, V _G =10V
R _g	Gate Poly Resistance	-	2	-	Ω	V _{DS} =0V, V _{GS} =0, f=1MHZ
C _{iss}	Input Capacitance	-	6900	-	pF	V _{DS} =30V, V _{GS} =0, f=1MHZ
C _{oss}	Output Capacitance	-	2600	-	pF	
C _{rss}	Reverse Transfer Capacitance	-	120	-	pF	
T _J , T _{STG}	Operating and Storage Temperature	-55°C to 175°C Max				